

Quantum Technologies (generic)

Utilizing defects in crystals for quantum information application (specific)



Kai-Mei Fu

Monday, July 30th, 2018

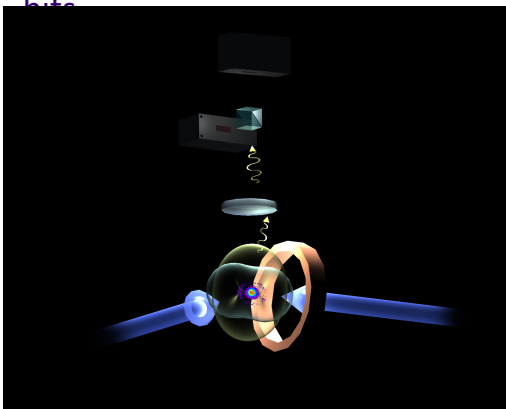
UW Physics REU program

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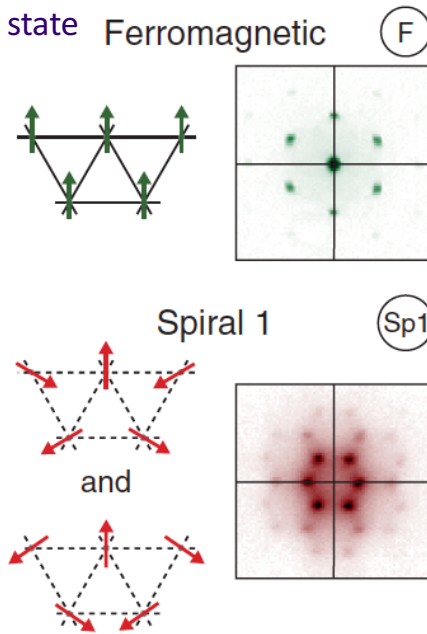
Atoms are the quintessential quantum system

Trapped ions as quantum bits



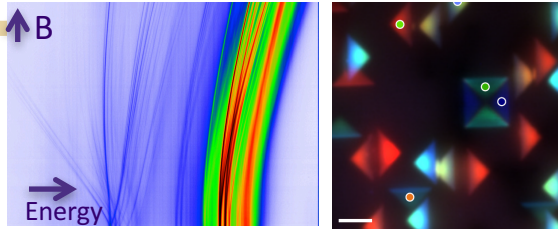
Schematic of a single trapped ion
Blinov group, UW

Cold atoms used to simulate magnetic effects in solid state

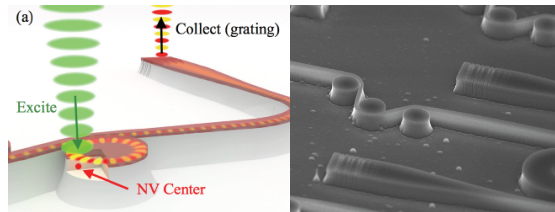


Sengstock group, Hamburg

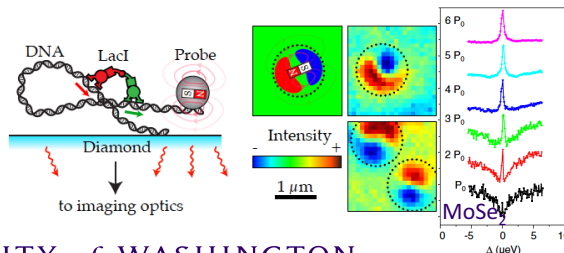
Quantum-enabled technologies



Fundamental properties of carriers bound to defects in direct band gap semiconductors

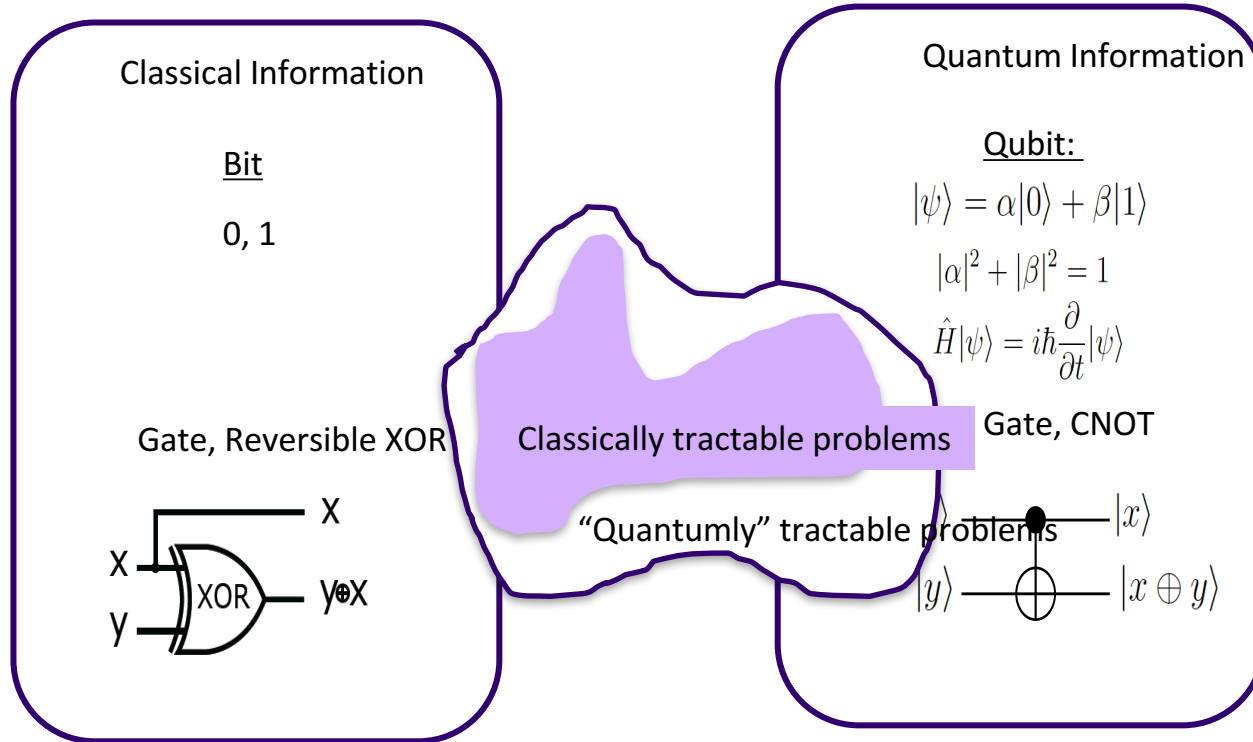


With “less-than-perfect” defects, building an on-chip network of spins



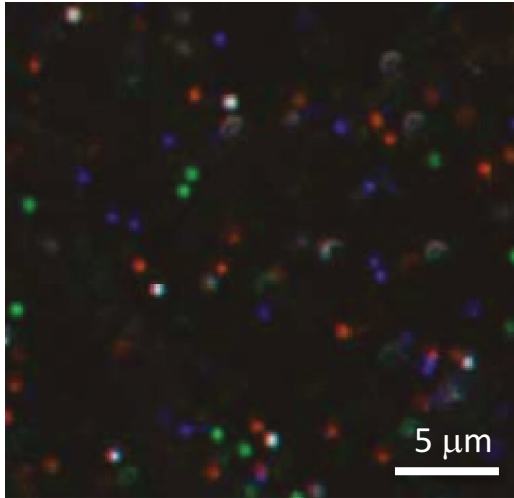
Collaborative efforts:
Sensing nanomagnet probes
(Paul Wiggins, UW)
Excitonic and magnetic properties in
2D materials (Xiaodong Xu, UW)

Quantum Information (brief diversion)



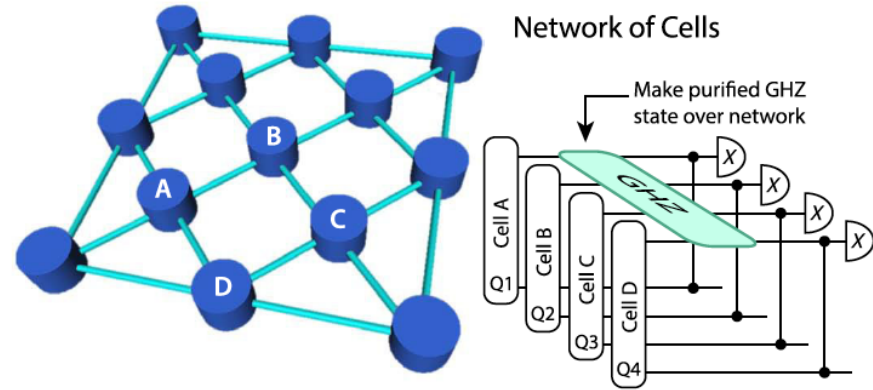
Defect-based quantum networks

Single defect experiments



Optical image of single defects in commercial diamond substrate¹.

Measurement-based quantum entanglement



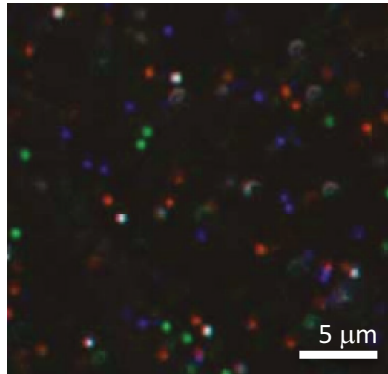
Distributed model of quantum information processing^{2,3}

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¹Edmonds *et al.* *PRB* (2012) ²Nickerson, Fitzsimons, Benjamin *PRX* 4 041041 (2014) ³Raussendorf, Briegel, *PRL* (2001)

Enabling developments for defect-based quantum information

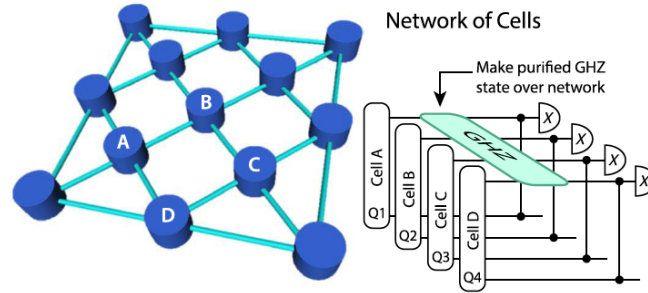
Single defect experiments



Optical image of single defects in commercial diamond substrate¹.

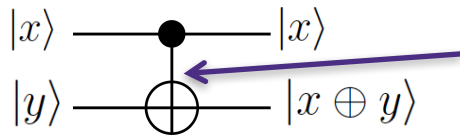
(Not just in diamond!)

Measurement-based quantum entanglement

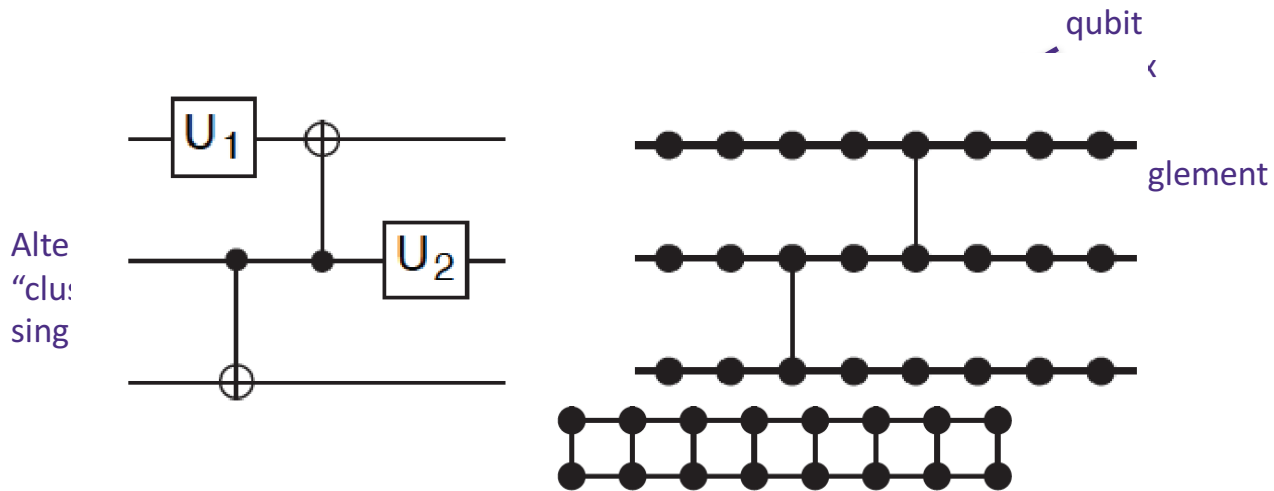


Distributed model of quantum information processing²

Removing the need for local interaction



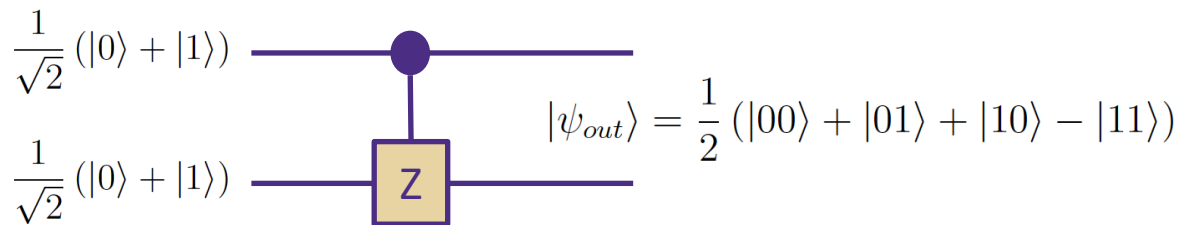
Looks like a local interaction that needs high level of control





(Significant portion of my research)

This edge is created when a c-phase gate is applied to the following input states.

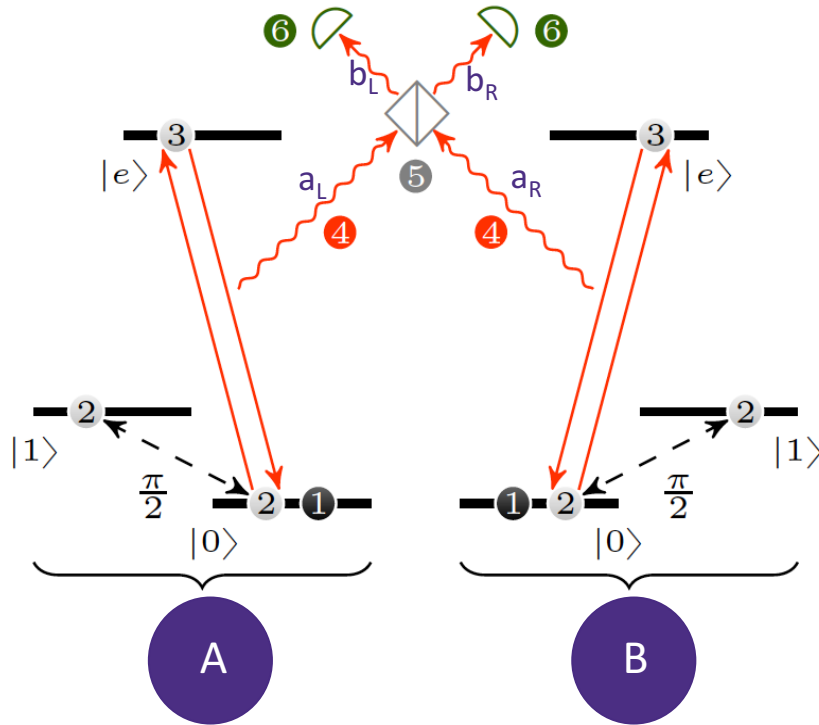


$$|\psi_{out}\rangle = \begin{bmatrix} 1 & 0 & 0 & 0 \\ 0 & 1 & 0 & 0 \\ 0 & 0 & 1 & 0 \\ 0 & 0 & 0 & -1 \end{bmatrix} \begin{bmatrix} \langle 00 | \psi_{in} \rangle \\ \langle 01 | \psi_{in} \rangle \\ \langle 10 | \psi_{in} \rangle \\ \langle 11 | \psi_{in} \rangle \end{bmatrix}$$

(Output state is local unitary equivalent to a Bell state.)



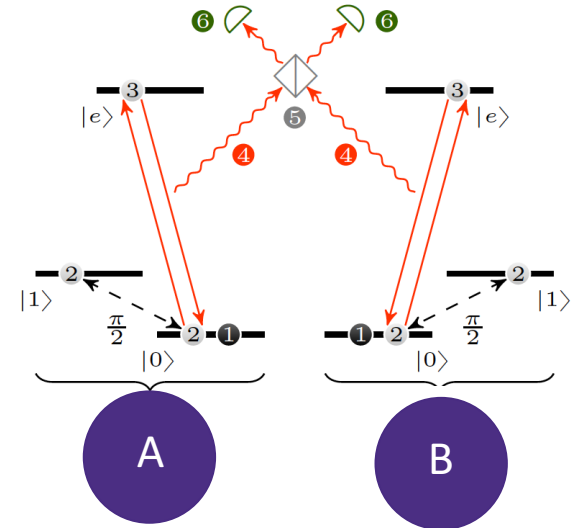
Edge can be created via measurement on emitted photons from A and B.



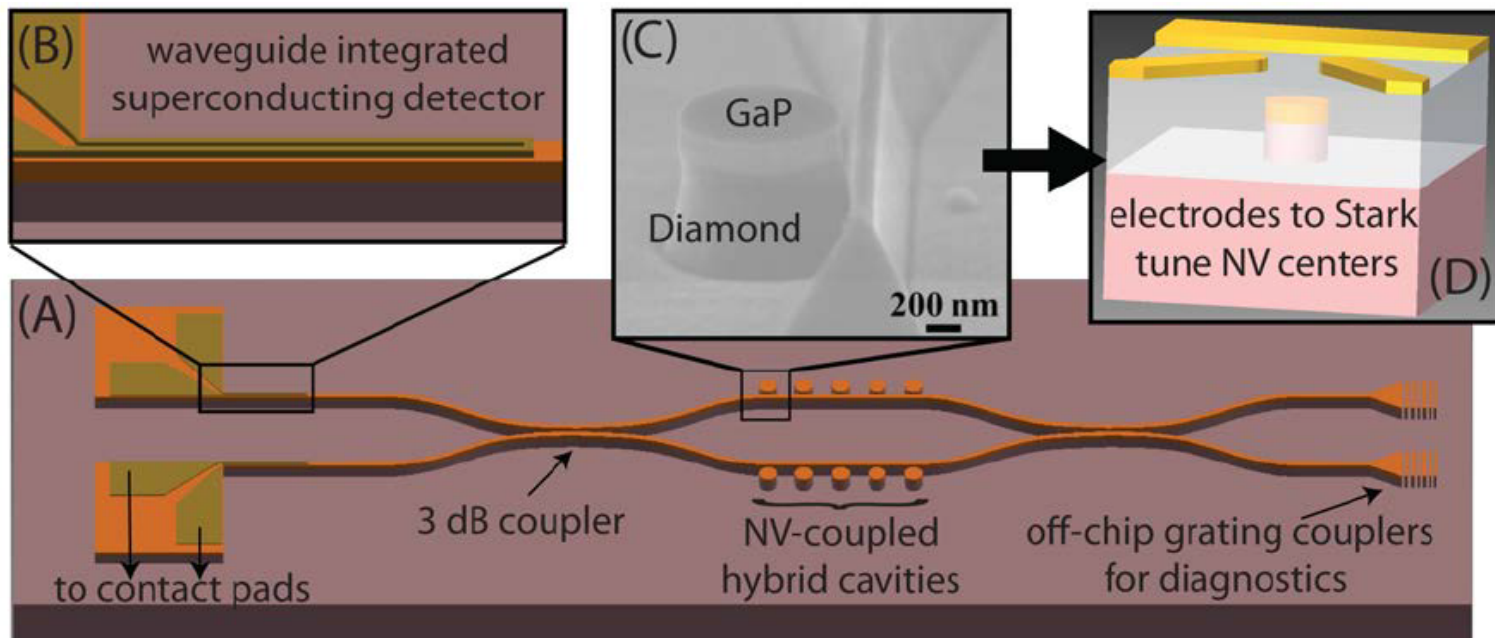
- 1 $[|0\rangle \otimes |0\rangle] |\text{vac}\rangle$
- 2 $[(|0\rangle + |1\rangle) \otimes (|0\rangle + |1\rangle)] |\text{vac}\rangle$
- 3 $[(|e\rangle + |1\rangle) \otimes (|e\rangle + |1\rangle)] |\text{vac}\rangle$
- 3' $[|e1\rangle + |1e\rangle] |\text{vac}\rangle$
- 4 $[|01\rangle a_R^\dagger + |10\rangle a_L^\dagger] |\text{vac}\rangle$
- 5 $[(|01\rangle + i|10\rangle) b_L^\dagger + (i|01\rangle + |10\rangle) b_R^\dagger] |\text{vac}\rangle$
- 6 $(|01\rangle + i|10\rangle)$

System requirements (subset)

- > **Two atoms must emit identical photons**
- > **Photon must be detected**
 - Described protocol scales linearly with detection efficiency
 - Protocols robust to loss error scale as square of efficiency
- > **At least 2 qubits per node with local operations**
- > **Entanglement rate should be significantly faster than decoherence time.**



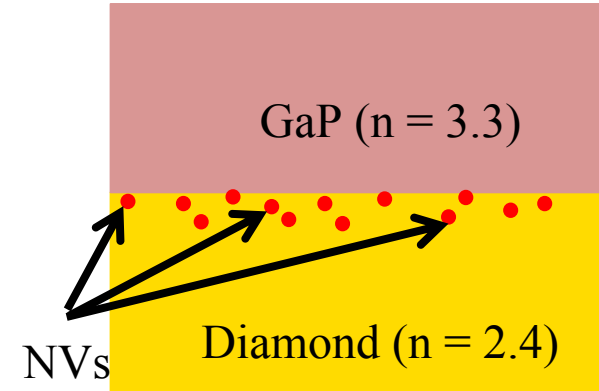
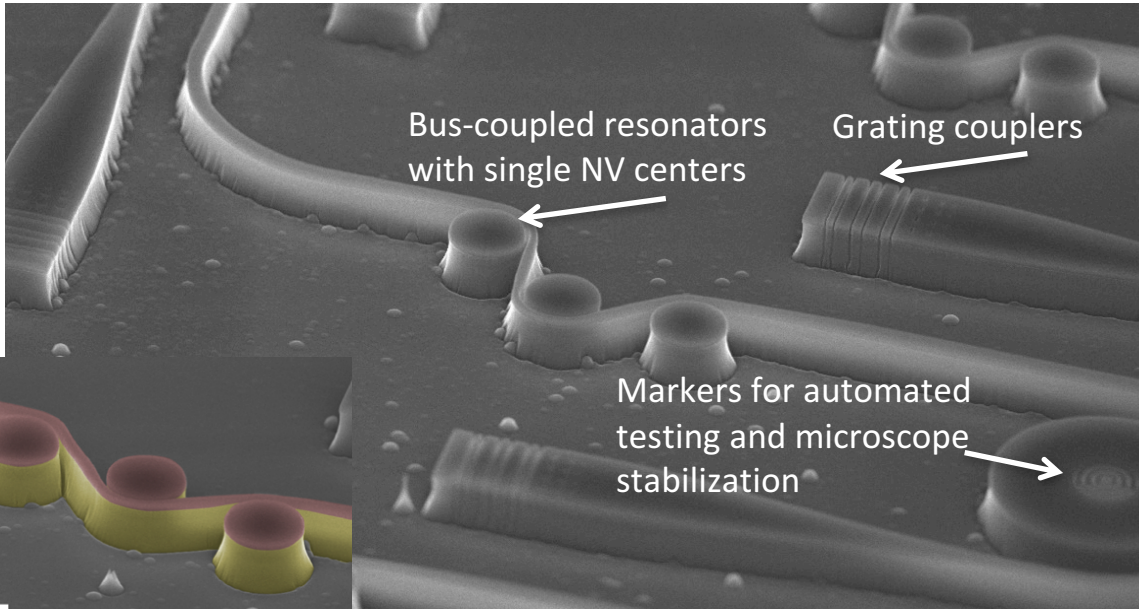
The lure of a solid-state platform



Efficient photon collection and routing



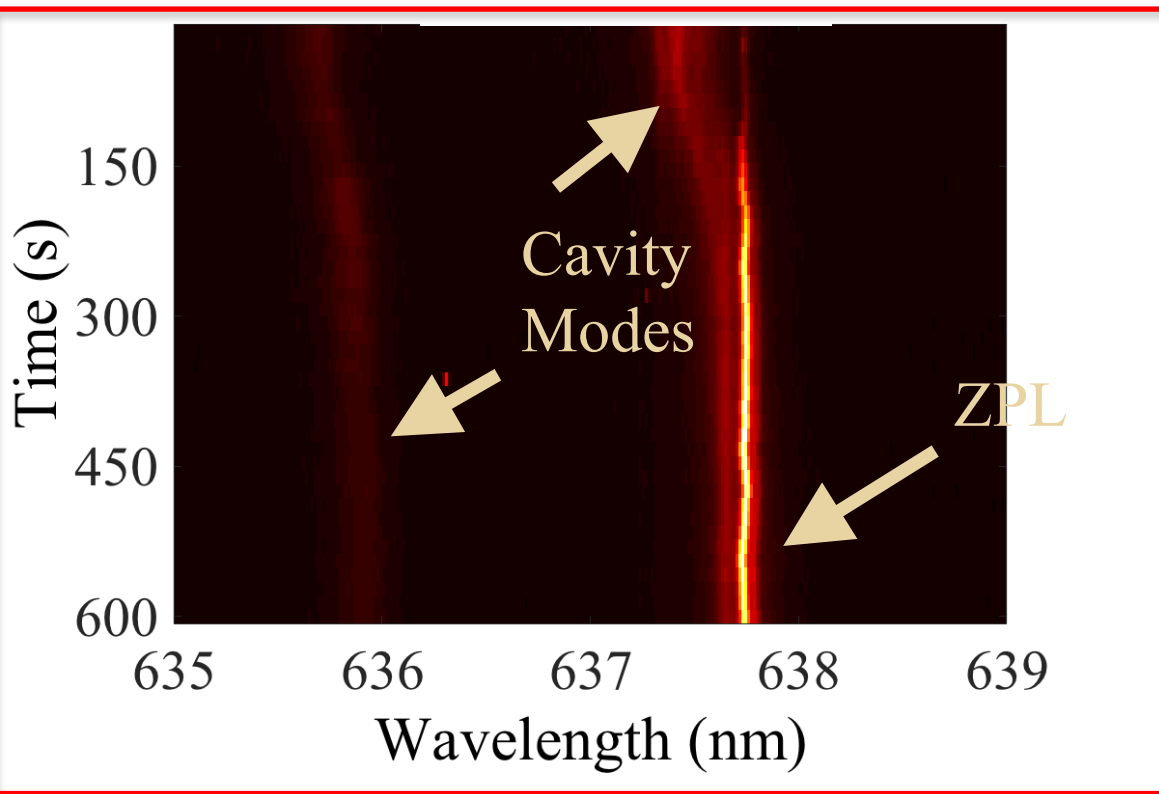
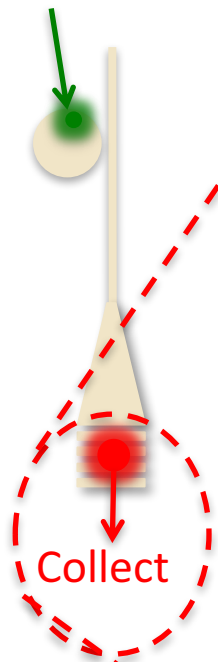
Mike Gould



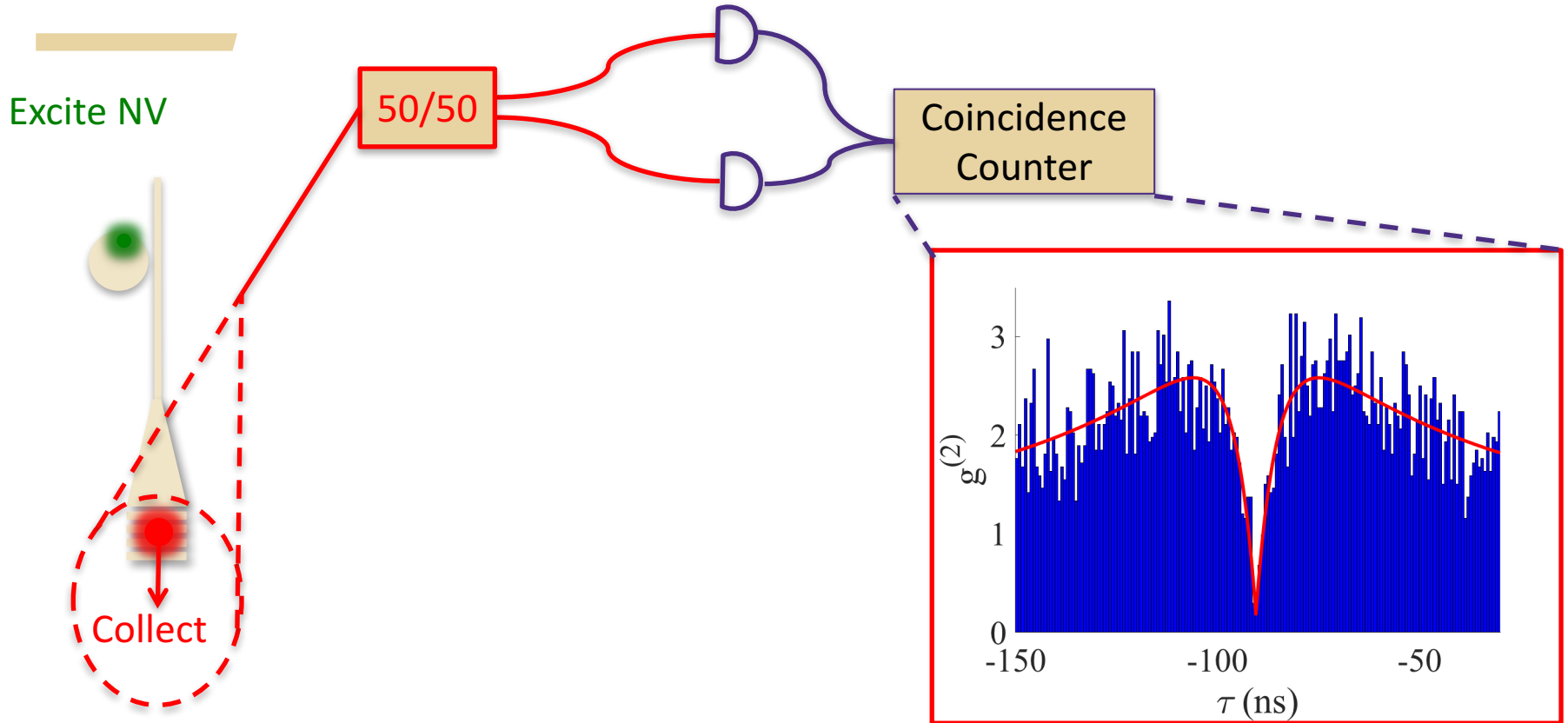
Gould et al., Physical Review Applied 2016, JOSA B 2016

Collecting photons from a single defect

Excite NV



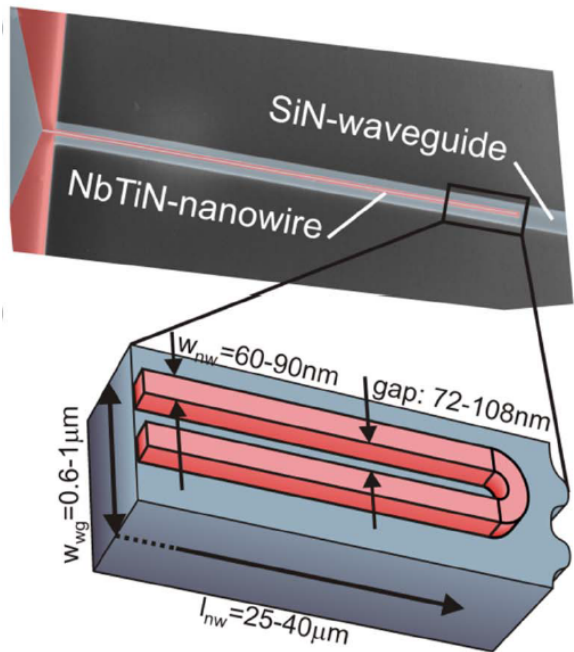
Statistics of a single photon source



Prospects for on-chip detection

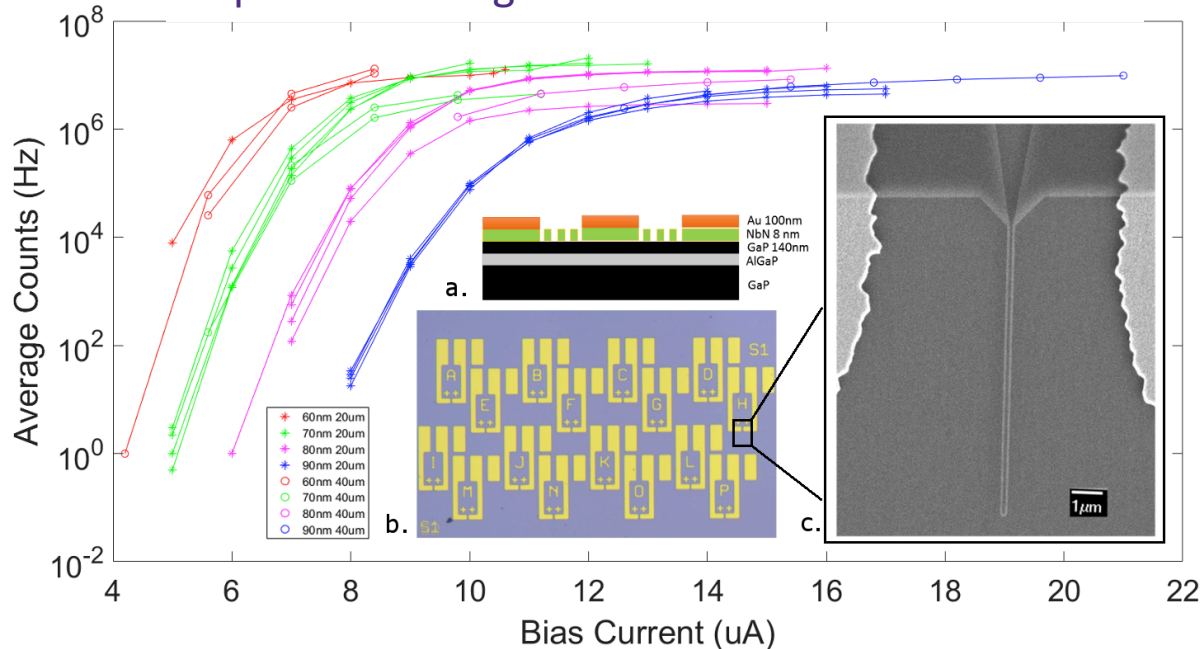


Srivatsa Chakravarthi



Hong Tang group, Yale

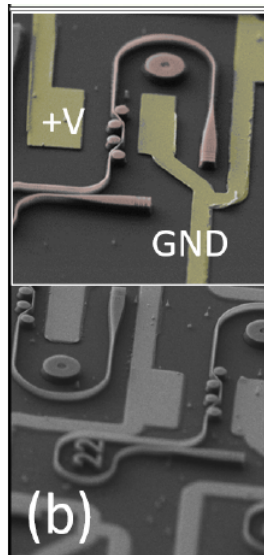
Superconducting NbN detectors on GaP at UW



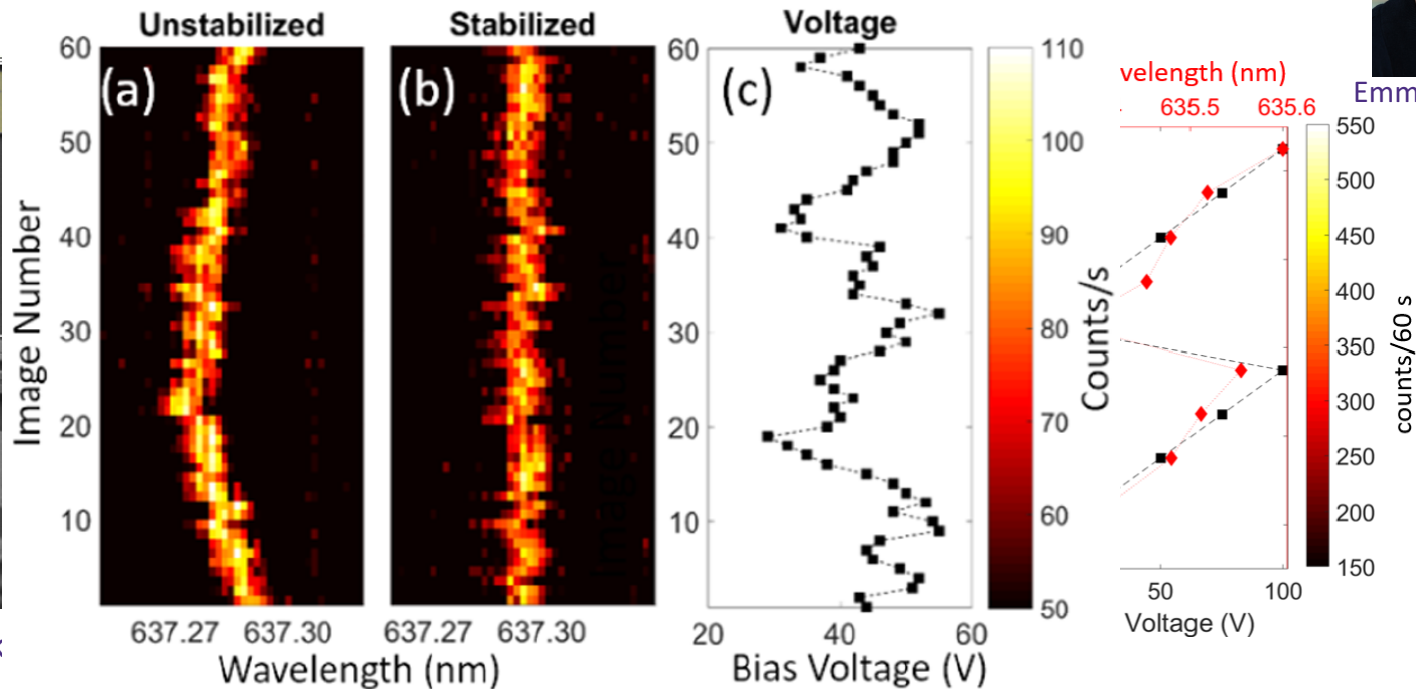
Prospects for active control of defect properties



Emma Schmidgall



Schmidgall, Chak

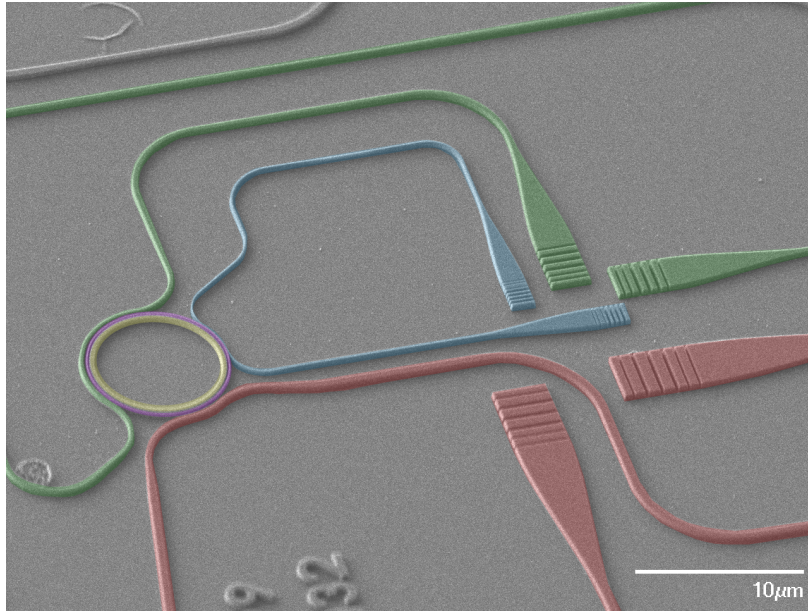


Disclaimer: level of stabilization is still orders of magnitude off for quantum applications.
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Low energy frequency conversion



Alan Logan



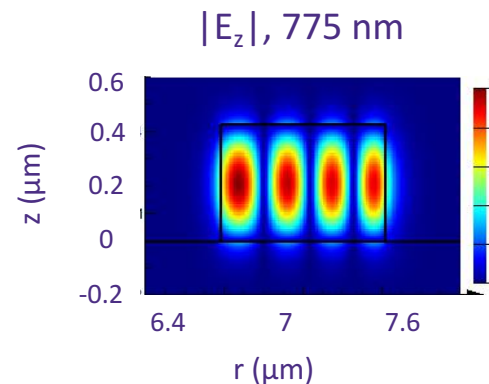
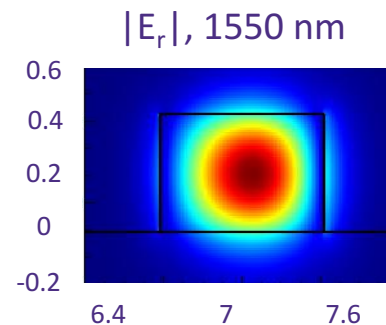
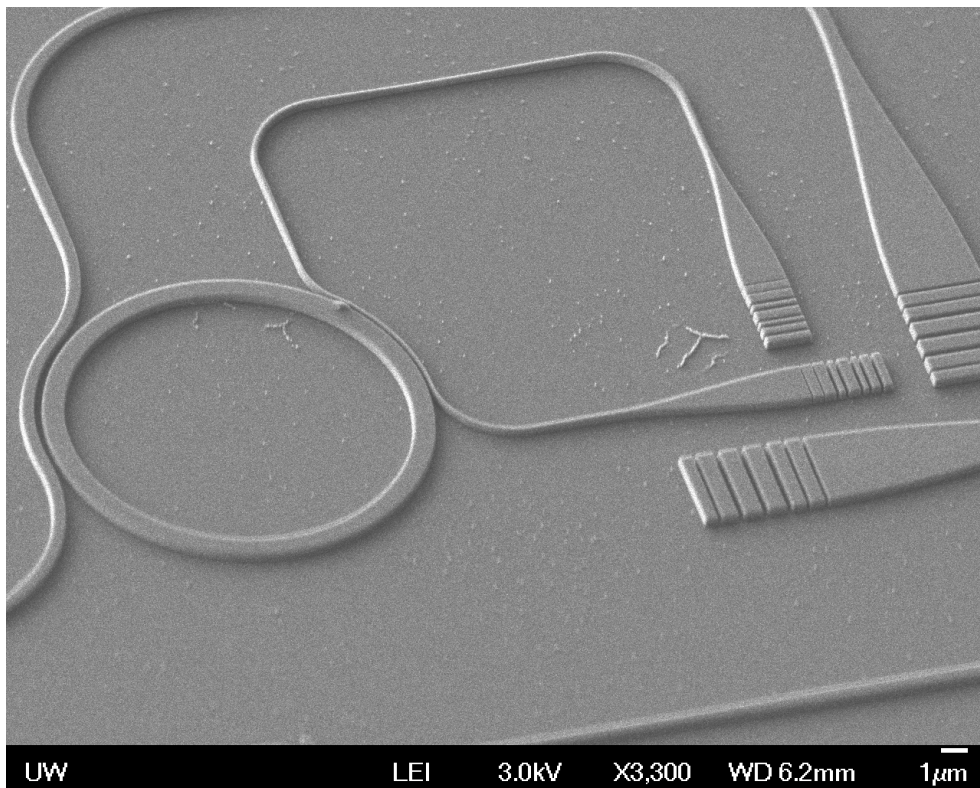
GaP transferred to oxide

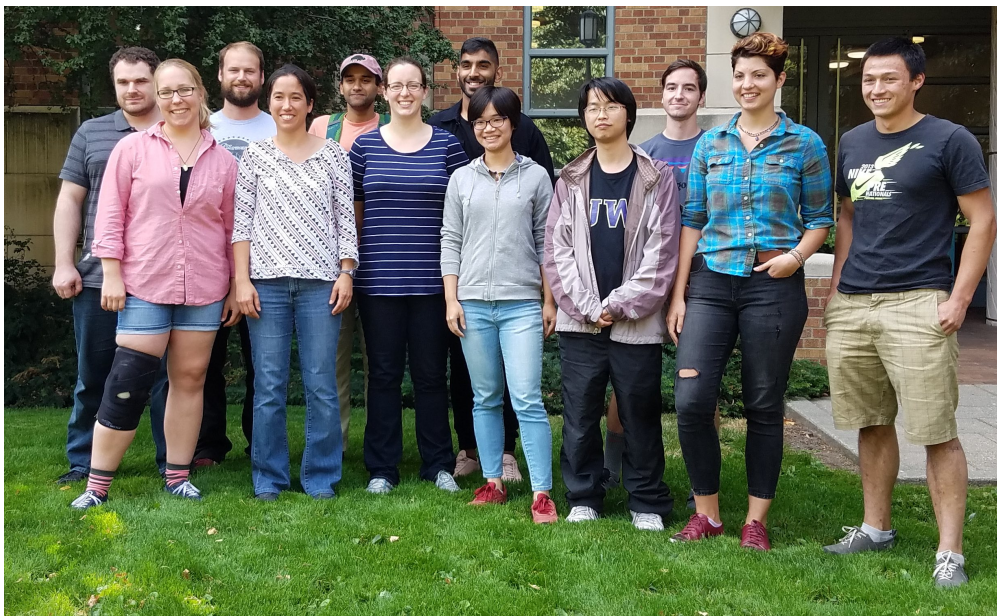
Difference frequency conversion:
 $637 \text{ nm} + 1080 \text{ nm} \rightarrow 1550 \text{ nm}$

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Nonlinear photonics design: Alejandro Rodriguez, Princeton

Low energy frequency conversion: Current working devices 1550 nm \rightarrow 775 nm





Semiconductor Spins

*Todd Karin, PhD

Xiayu Linpeng, grad

Maria Viitaniemi, grad

*Cameron Johnson, undergrad

Colin Stanley, Glasgow (GaAs growth)

Satoru Seto, Ishikawa (CdTe growth)

Simon Watkins, Simon Fraser (InP growth)

Y. Kozuka, M.Kawasaki, U. Tokyo (ZnO growth)

Mikhail Durnev, Ioffe (theory)

Mikhael Glazov, (theory)

Diamond Photonics

Michael Gould*, PhD

Emma Schmidgall, postdoc

Srivatsa Vardaraj, grad

Alan Logan, grad

Ian Christen, undergrad

Fariba Hatami, Humboldt (GaP growth)

Andrea Fiore (NbN growth)

Funding



*former members